

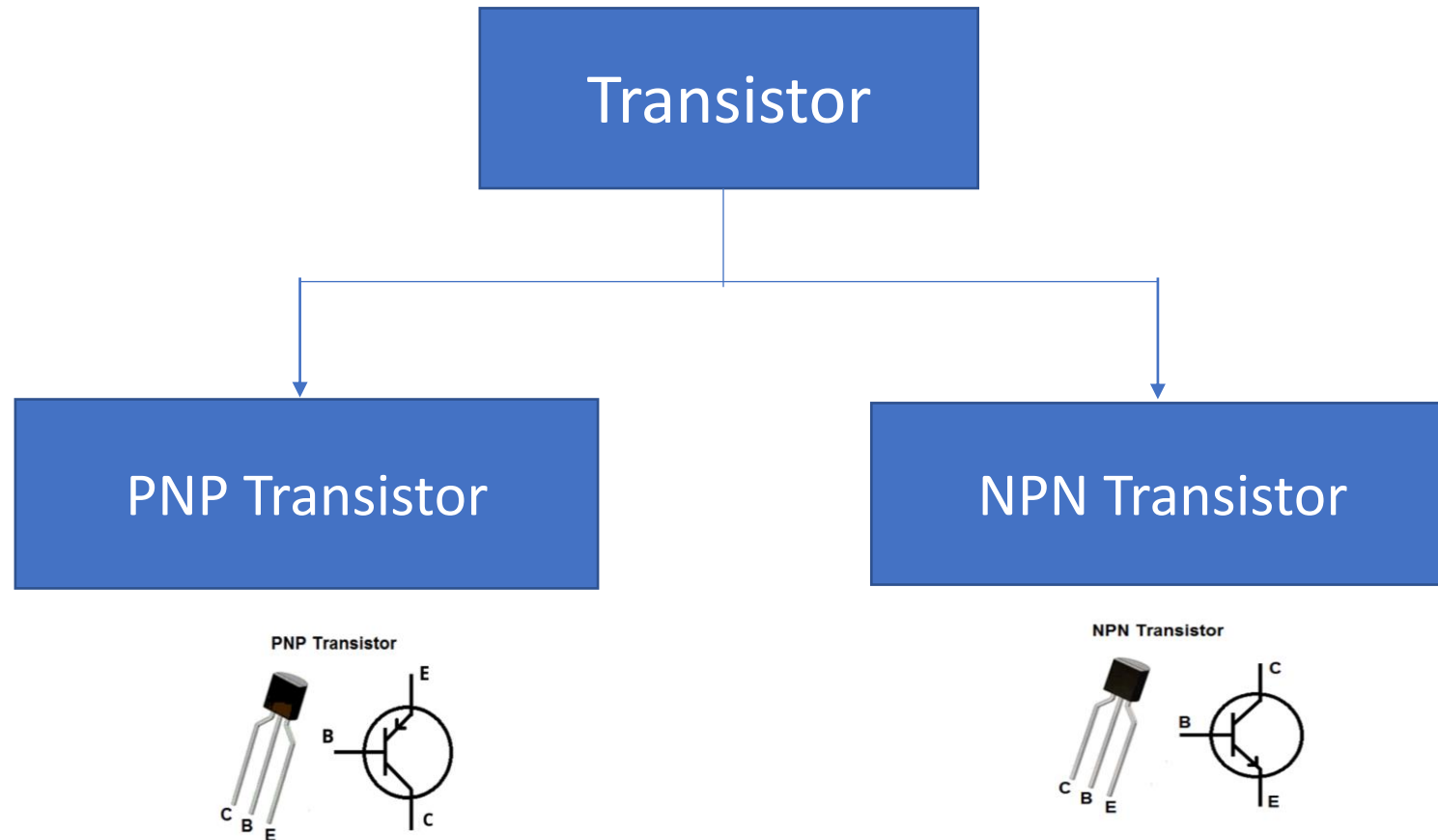
Transistor

Lecture 6

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Definition of Transistor :

Transistor is a three electrode device capable of amplification in addition of rectification. It is the basic building block in modern electronics



A junction transistor is made up of a semiconductor such as *Ge* or *Si* in which a *P-type* thin layer is sandwiched between two *N-type* layers. The transistor so formed is called *N – P – N* transistor. Alternately a transistor can also have an *N-type* layer between two *P-type* layers. The transistor is then termed a *P – N – P* transistor. *P – N – P* and *N – P – N* transistor are systematically shown in *Fig 1 and Fig 2*. The middle portion of the transistor is called the ***Base*** and the two end portions are known as ***Emitter*** and ***Collector***. The emitter-base junction is usually referred as emitter junction J_E and the collector-base junction as the collector junction J_C . The size of the transistor is quite small.

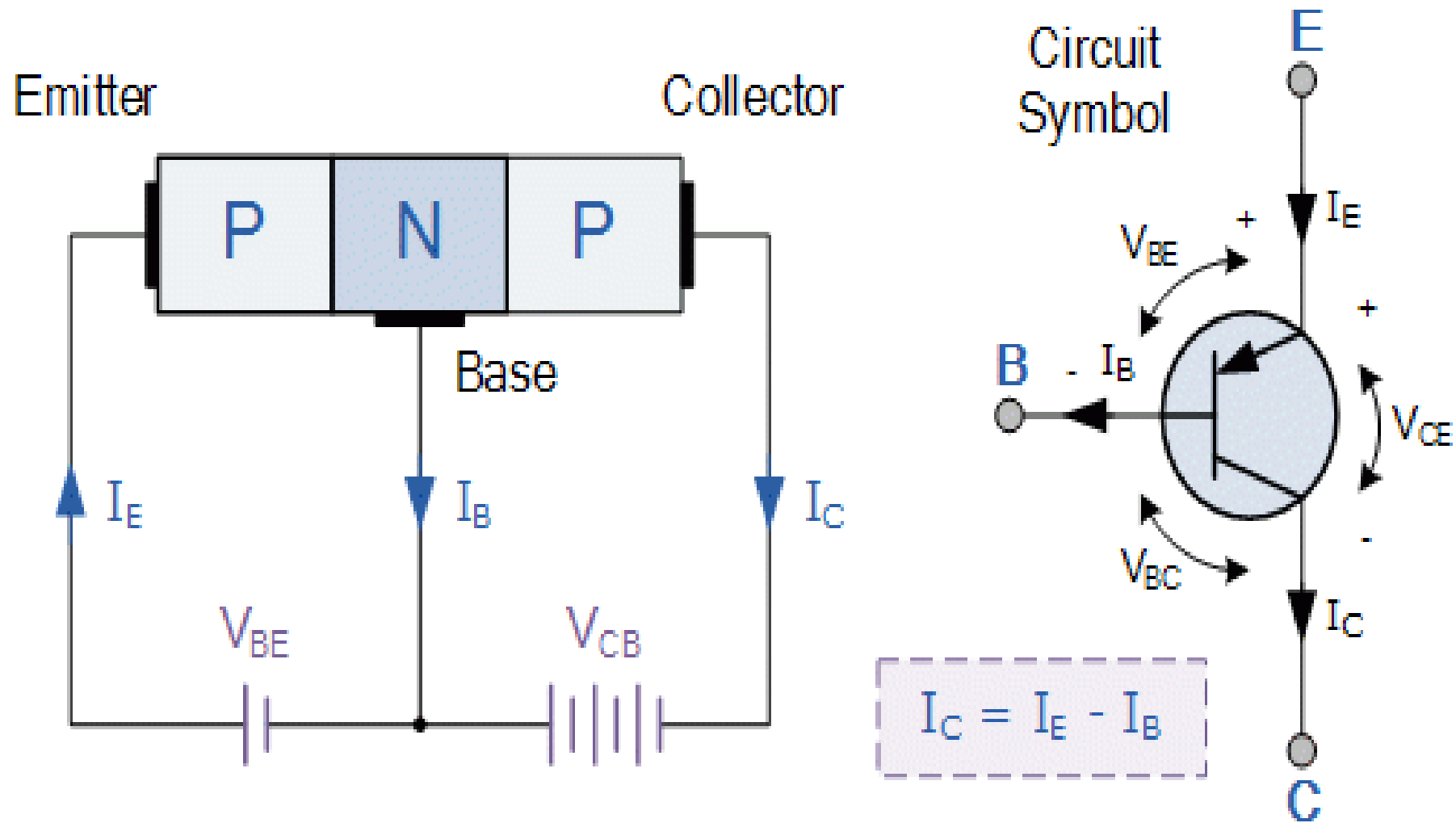


Fig 1

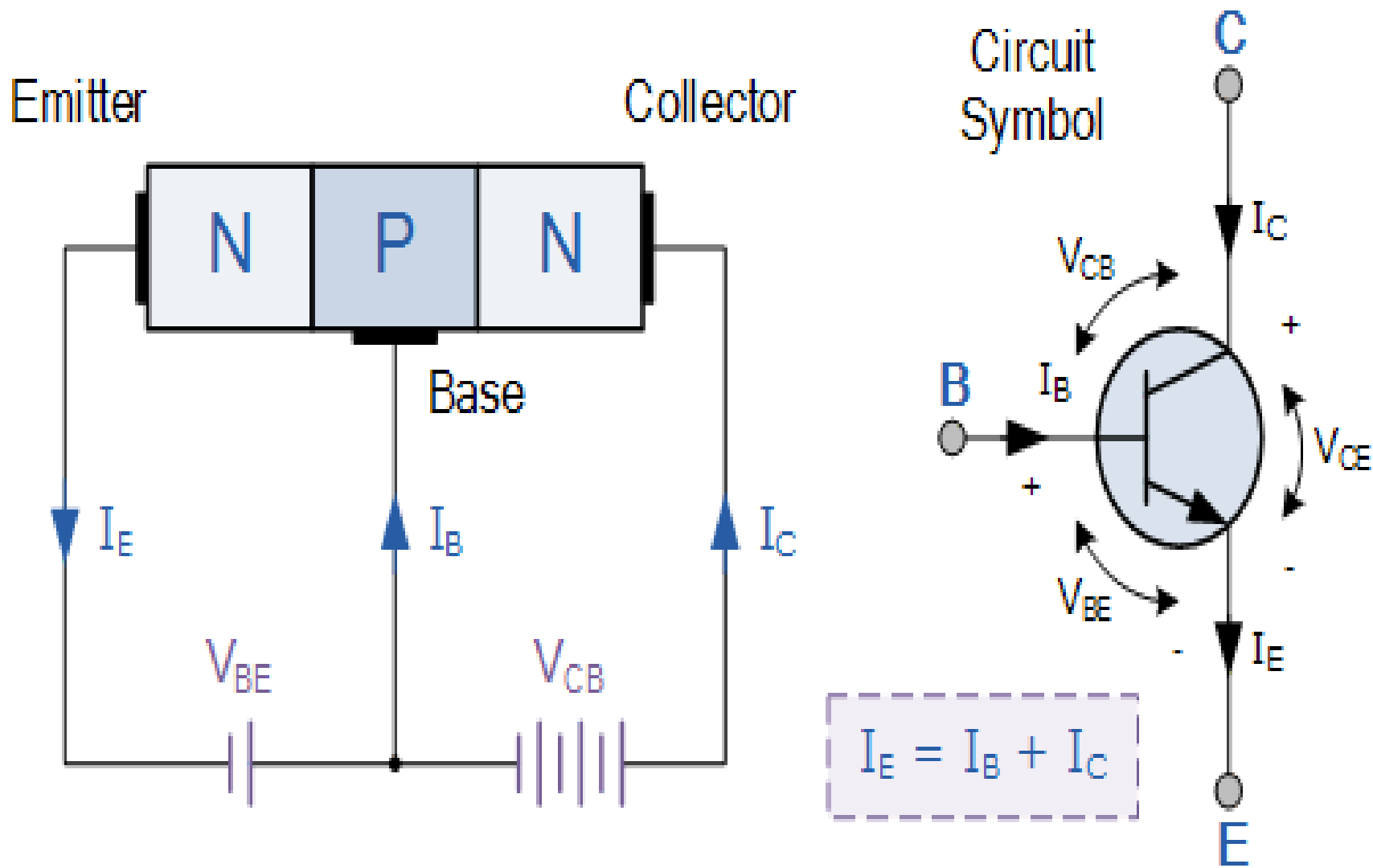


Fig 2

The structure is sealed inside a metal or plastic case to protect it from moisture. Metal leads E , B and C come out of the package for connection to the *emitter*, the *base* and the *collector* respectively. Since both the majority and minority carriers are involved in a junction transistor the device is termed as *bipolar junction transistor (BJT)*, *bipolar transistor* or *bipolar device*.

In the normal transistor operation *emitter – base* junction is forward biased and the *collector – base* junction is reversed biased. The current enters the transistor through the emitter terminal for a $P - N - P$ transistor. On the other hand current leaves the transistor through the for an $N - P - N$ transistor.

In both case the *emitter, base and collector* currents I_E , I_B and I_C respectively are taken positive when the currents go into the transistor. The symbols V_{EB} , V_{CB} and V_{CE} represent respectively the *emitter – base, collector – base* and *collector – emitter* voltages.

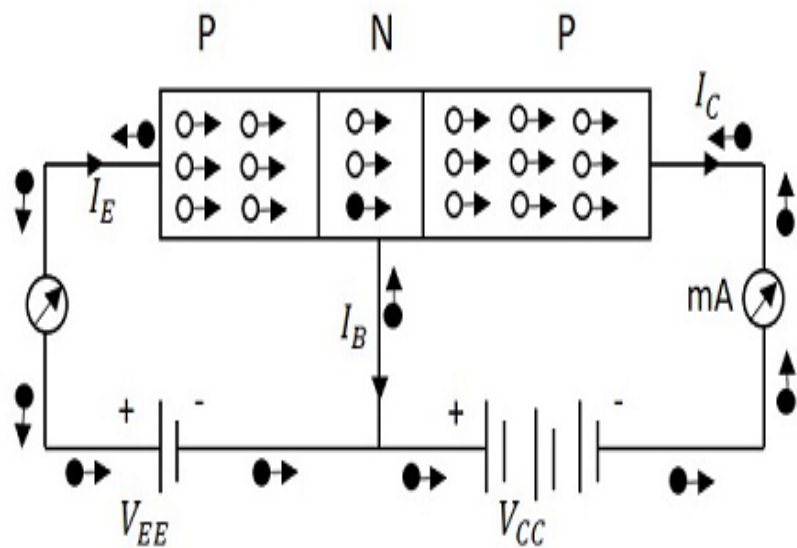


Fig 3

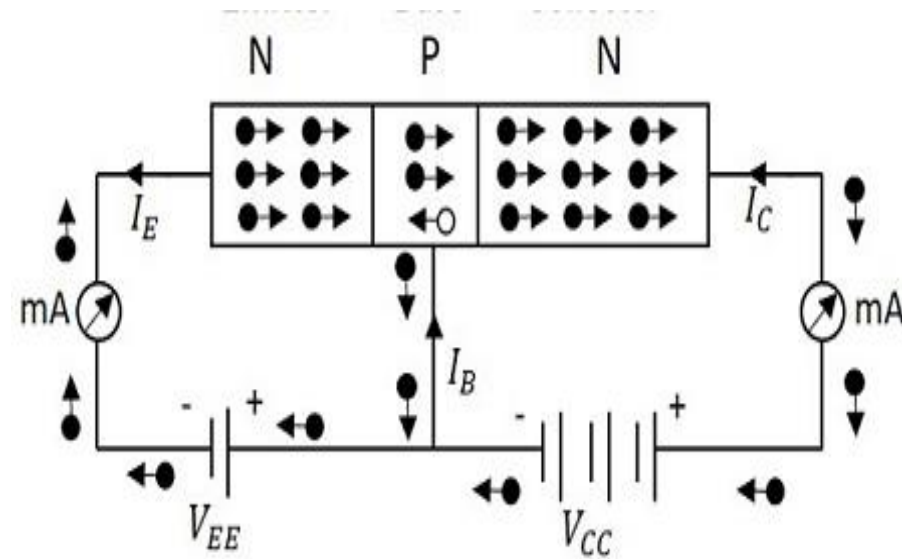


Fig 4

Three points are important for $P - N - P$ transistor

- a) The conduction in $P - N - P$ transistor takes place through holes.
- b) The collector current is slightly less than the emitter current
- c) The increase or decrease in *emitter current* affects the *collector current*.

Similarly the operation of $N - P - N$ transistor can be explained by *Fig 4*, in which *emitter - base* junction forward biased and *collector - base* junction is reversed biased. The V_{EE} provides negative potential at the emitter which repels the electrons in the $N - type$ material and these electrons cross the emitter-base junction to reach the base region. This flow slowly increases and the electron current flows through the transistor.

The points are important for $N - P - N$ transistor

The conduction in a $N - P - N$ transistor takes place through electrons.

The collector current is higher than the emitter current.

The increase or decrease in the emitter current affects the collector current.

The amplification factor α and β may be defined as

$$\alpha = \left(\frac{\partial I_C}{\partial I_E} \right) \rightarrow (i), \text{ when } V_{CB} \text{ is constant}$$
$$\beta = \left(\frac{\partial I_C}{\partial I_B} \right) \rightarrow (ii), \text{ when } V_{CE} \text{ is constant}$$

By definition $\Delta I_C = \alpha \cdot \Delta I_E$

The magnitude of emitter current is equal to sum of collector and base current. Thus

$$|\Delta I_E| = |\Delta I_C| + |\Delta I_B| = |\alpha I_E| + |\Delta I_B|$$

$$\Rightarrow \Delta I_B = \Delta I_E(1 - \alpha)$$

$$\Rightarrow \frac{\Delta I_B}{\Delta I_C} = \frac{\Delta I_E}{\Delta I_C}(1 - \alpha)$$

$$\Rightarrow \frac{1}{\beta} = \frac{1}{\alpha}(1 - \alpha)$$

$$\Rightarrow \beta = \frac{\alpha}{1 - \alpha} \rightarrow (iii)$$